

# MOS FIELD EFFECT TRANSISTOR **2SJ647**

# P-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR SWITCHING

## **DESCRIPTION**

The 2SJ647 is a switching device which can be driven directly by a 2.5 V power source.

The 2SJ647 features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

## **FEATURES**

- 2.5 V drive available
- · Low on-state resistance

RDS(on)1 = 1.45  $\Omega$  MAX. (VGS = -4.5 V, ID = -0.2 A)

RDS(on)2 = 1.55  $\Omega$  MAX. (VGS = -4.0 V, ID = -0.2 A)

RDS(on)3 =  $2.98 \Omega$  MAX. (VGS = -2.5 V, ID = -0.15 A)

# **ORDERING INFORMATION**

PART NUMBER	PACKAGE
2SJ647	SC-70 (SSP)

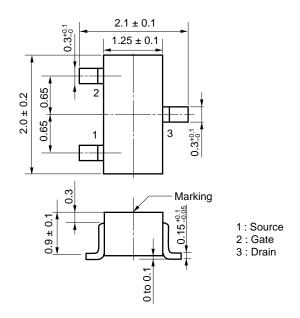
Remark Marking: H22

ABSOLUTE MAXIMUM RATINGS (TA = 25°C)  Drain to Source Voltage (Vgs = 0 V) Vgss -20 V  Gate to Source Voltage (Vps = 0 V) Vgss 712 V				
Drain to Source Voltage (Vgs = 0 V)	VDSS	-20	V	
Gate to Source Voltage (VDS = 0 V)	Vgss	∓12	V	
Drain Current (DC) (T <sub>A</sub> = 25°C)	ID(DC)	∓0.4	Α	
Drain Current (pulse) Note1	ID(pulse)	∓1.6	Α	
Total Power Dissipation Note2	Рт	0.2	W	
Channel Temperature	Tch	150	°C	
Storage Temperature	$T_{stg}$	-55 to +150	°C	

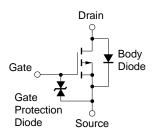
**Notes 1.** PW  $\leq$  10  $\mu$ s, Duty Cycle  $\leq$  1%

2. Mounted on FR-4 board of 2500 mm<sup>2</sup> x 1.1 mm.

# **PACKAGE DRAWING (Unit: mm)**



# **EQUIVALENT CIRCUIT**



# Remark

The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

Caution This product is electrostatic-sensitive device due to low ESD capability and should be handled with caution for electrostatic discharge.

VESD ±100 V TYP. at C = 200 pF, R = 0, Single Pulse.

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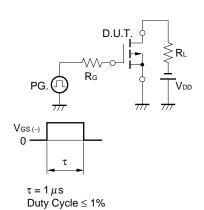
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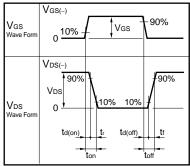


# **ELECTRICAL CHARACTERISTICS (TA = 25°C)**

CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	Ipss	V <sub>DS</sub> = -20 V, V <sub>GS</sub> = 0 V			-1.0	μΑ
Gate Leakage Current	Igss	V <sub>GS</sub> = ∓12 V, V <sub>DS</sub> = 0 V			∓10	μΑ
Gate Cut-off Voltage	V <sub>GS(off)</sub>	$V_{DS} = -10 \text{ V}, I_{D} = -1.0 \text{ mA}$	-0.8	-1.3	-1.8	V
Forward Transfer Admittance	<b>y</b> fs	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -0.2 A	0.2	0.6		S
Drain to Source On-state Resistance	RDS(on)1	V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -0.2 A		1.17	1.45	Ω
	RDS(on)2	V <sub>GS</sub> = -4.0 V, I <sub>D</sub> = -0.2 A		1.25	1.55	Ω
	RDS(on)3	V <sub>GS</sub> = -2.5 V, I <sub>D</sub> = -0.15 A		2.25	2.98	Ω
Input Capacitance	Ciss	Vps = -10 V		29		pF
Output Capacitance	Coss	V <sub>G</sub> S = 0 V		15		pF
Reverse Transfer Capacitance	Crss	f = 1.0 MHz		3		pF
Turn-on Delay Time	td(on)	V <sub>DD</sub> = -10 V, I <sub>D</sub> = -0.2 A		23		ns
Rise Time	tr	Vgs = -4.0 V		39		ns
Turn-off Delay Time	t <sub>d(off)</sub>	R <sub>G</sub> = 10 Ω		50		ns
Fall Time	<b>t</b> f			33		ns
Body Diode Forward Voltage	V <sub>F(S-D)</sub>	IF = 0.4 A, Vgs = 0 V		0.93		V

# TEST CIRCUIT SWITCHING TIME



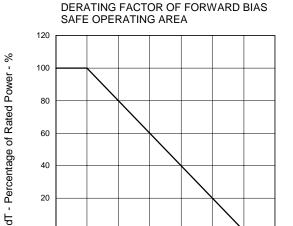


0

0

25

# TYPICAL CHARACTERISTICS (TA = 25°C)



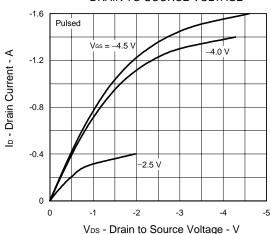
DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE

TA - Ambient Temperature - °C

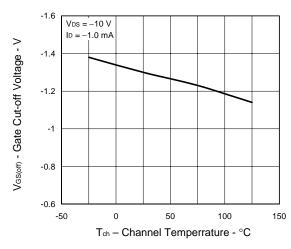
100

125

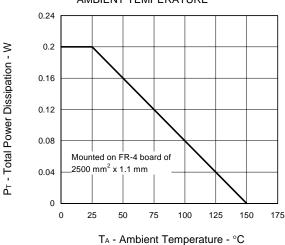
175



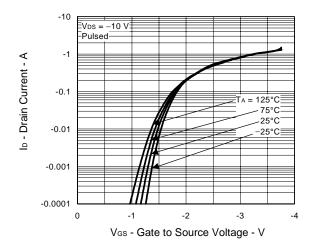
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



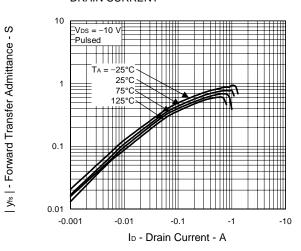
TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



FORWARD TRANSFER CHARACTERISTICS



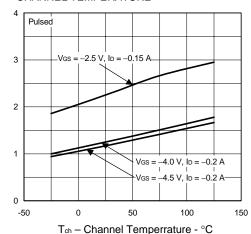
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



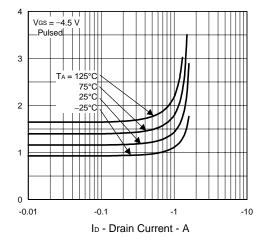
RDS(m) - Drain to Source On-state Resistance

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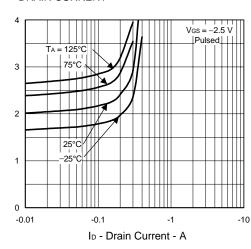
## DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



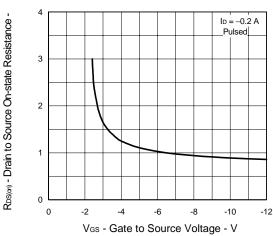
# DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



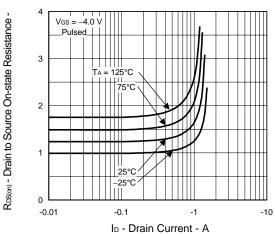
# DRAIN TO SOURCE ON-STATE RESISTANCE vs. **DRAIN CURRENT**



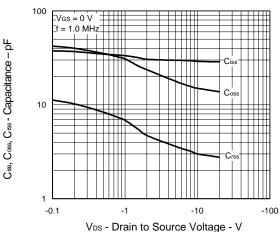
# DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



# DRAIN TO SOURCE ON-STATE RESISTANCE vs. **DRAIN CURRENT**

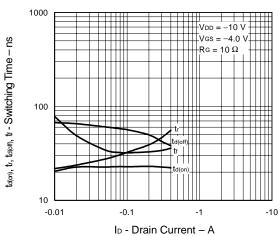


#### CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE

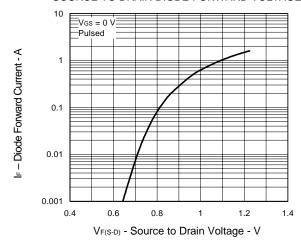


 $\mathsf{Ros}_{(\sigma)}$  - Drain to Source On-state Resistance -  $m\Omega$ 

# SWITCHING CHARACTERISTICS



# SOURCE TO DRAIN DIODE FORWARD VOLTAGE



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